

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

524,288-WORD BY 8-BIT CMOS STATIC RAM

DESCRIPTION

The TC55V8512J/FT is a 4,194,304-bit high-speed static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed, it operates from a single 3.3 V power supply. Chip enable (\overline{CE}) can be used to place the device in a low-power mode, and output enable (\overline{OE}) provides fast memory access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly LVTTL compatible. The TC55V8512J/FT is available in plastic 36-pin SOJ and 44-pin TSOP with 400mil width for high density surface assembly.

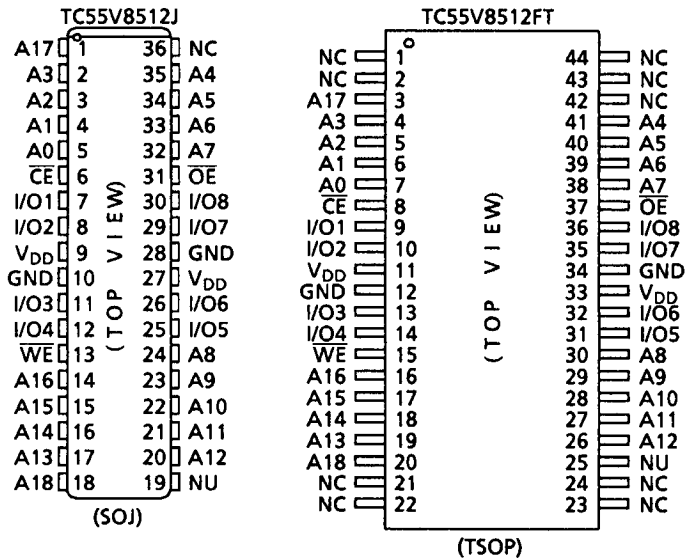
FEATURES

- Fast access time (the following are maximum values)
 - TC55V8512J/FT-12: 12 ns
 - TC55V8512J/FT-15: 15 ns
- Low-power dissipation (the following are maximum values)

Cycle Time	12	15	20	25	ns
Operation (max)	170	140	130	110	mA
- Single power supply voltage of $3.3V \pm 0.3V$
- Fully static operation
- All inputs and outputs are LVTTL compatible
- Output buffer control using \overline{OE}
- Package:
 - SOJ36-P-400-1.27 (J) (Weight: 1.35g typ)
 - TSOP II 44-P-400-0.80 (FT) (Weight: 0.45g typ)

Standby: 4 mA (both devices)

PIN ASSIGNMENT



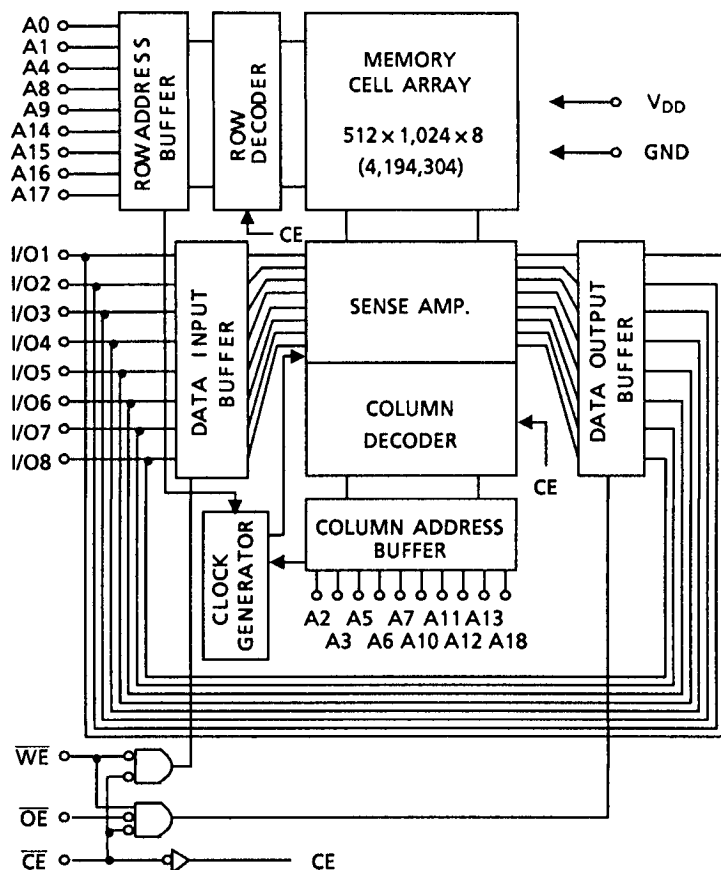
PIN NAMES

A0 to A18	Address Inputs
I/O1 to I/O8	Data Inputs/Outputs
\overline{CE}	Chip Enable Input
\overline{WE}	Write Enable Input
\overline{OE}	Output Enable Input
V _{DD}	Power (+ 3.3V)
GND	Ground
NC	No Connection
NU	Not Usable (Input)

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BLOCK DIAGRAM



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	- 0.5 to 4.6	V
V _{IN}	Input Terminal Voltage	- 0.5* to 4.6	V
V _{I/O}	Input/Output Terminal Voltage	- 0.5* to V _{DD} + 0.5**	V
P _D	Power Dissipation	1.4	W
T _{solder}	Soldering Temperature (10s)	260	°C
T _{strg}	Storage Temperature	- 65 to 150	°C
T _{opr}	Operating Temperature	- 10 to 85	°C

* : -1.5V with a pulse width of 20% · t_{RC} min (4ns max)
 ** : V_{DD}+1.5V with a pulse width of 20% · t_{RC} min (4ns max)

DC RECOMMENDED OPERATING CONDITIONS (T_a = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V _{DD}	Power Supply Voltage	3.0	3.3	3.6	V
V _{IH}	Input High Voltage	2.0	-	V _{DD} + 0.3**	V
V _{IL}	Input Low Voltage	- 0.3*	-	0.8	V

* : -1.0V with a pulse width of 20% · t_{RC} min (4ns max)
 ** : V_{DD}+1.0V with a pulse width of 20% · t_{RC} min (4ns max)

DC CHARACTERISTICS (Ta = 0° to 70°C, V_{DD} = 3.3V ± 0.3V)

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT	
I _{IL}	Input Leakage Current (Except NU pin)	V _{IN} = 0 to V _{DD}	-1	-	1	μA	
I _{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IL}$ or $\overline{OE} = V_{IH}$ V _{OUT} = 0 to V _{DD}	-1	-	1	μA	
I _{I(NU)}	Input Current (NU pin)	V _{IN} = 0 to 0.8V	-1	-	20	μA	
		V _{IN} = 0 to 0.2V	-1	-	1		
V _{OH}	Output High Voltage	I _{OH} = -2mA	2.4	-	-	V	
		I _{OH} = -100μA	V _{DD} - 0.2	-	-		
V _{OL}	Output Low Voltage	I _{OL} = 2mA	-	-	0.4		
		I _{OL} = 100μA	-	-	0.2		
I _{DDO}	Operating Current	$\overline{CE} = V_{IL}$, I _{out} = 0mA $\overline{OE} = V_{IH}$ Other Inputs = V _{IH} / V _{IL}	tcycle = 12ns	-	-	170	mA
			tcycle = 15ns	-	-	140	
			tcycle = 20ns	-	-	130	
			tcycle = 25ns	-	-	110	
I _{DDS1}	Standby Current	$\overline{CE} = V_{IH}$, Other Inputs = V _{IH} or V _{IL}	-	-	50	mA	
I _{DDS2}		$\overline{CE} = V_{DD} - 0.2V$ Other Inputs = V _{DD} - 0.2V or 0.2V	-	-	4		

CAPACITANCE (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	6	pF
C _{I/O}	Input/Output Capacitance	V _{I/O} = GND	8	pF

Note: This parameter is periodically sampled and is not 100% tested.

OPERATING MODE

MODE	\overline{CE}	\overline{OE}	\overline{WE}	I/O1 to I/O8	POWER
Read	L	L	H	Output	I _{DDO}
Write	L	x	L	Input	I _{DDO}
Outputs Disable	L	H	H	High Impedance	I _{DDO}
Standby	H	x	x	High Impedance	I _{DDS}

x: Don't care

Note: The NU pin must be left unconnected or tied to GND or a voltage level of less than 0.8 V. You must not apply a voltage of more than 0.8 V to the NU.

AC CHARACTERISTICS (Ta = 0° to 70°C (Note 1), V_{DD} = 3.3V ± 0.3V)

READ CYCLE

SYMBOL	PARAMETER	TC55V8512J/FT-12		TC55V8512J/FT-15		UNIT
		MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	12	-	15	-	ns
t _{ACC}	Address Access Time	-	12	-	15	
t _{CO}	Chip Enable Access Time	-	12	-	15	
t _{OE}	Output Enable Access Time	-	6	-	8	
t _{OH}	Output Data Hold Time from Address Change	3	-	4	-	
t _{COE}	Output Enable Time from Chip Enable	3	-	4	-	
t _{OEE}	Output Enable Time from Output Enable	1	-	1	-	
t _{COD}	Output Disable Time from Chip Enable	-	7	-	8	
t _{ODO}	Output Disable Time from Output Enable	-	7	-	8	

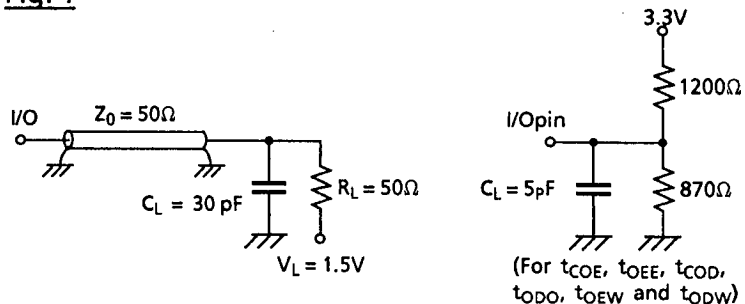
WRITE CYCLE

SYMBOL	PARAMETER	TC55V8512J/FT-12		TC55V8512J/FT-15		UNIT
		MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	12	-	15	-	ns
t _{WP}	Write Pulse Width	8	-	9	-	
t _{CW}	Chip Enable to End of Write	10	-	12	-	
t _{AW}	Address Valid to End of Write	10	-	12	-	
t _{AS}	Address Setup Time	0	-	0	-	
t _{WR}	Write Recovery Time	0	-	0	-	
t _{DS}	Data Setup Time	7	-	8	-	
t _{DH}	Data Hold Time	0	-	0	-	
t _{OEW}	Output Enable Time from Write Enable	1	-	1	-	
t _{ODW}	Output Disable Time from Write Enable	-	7	-	8	

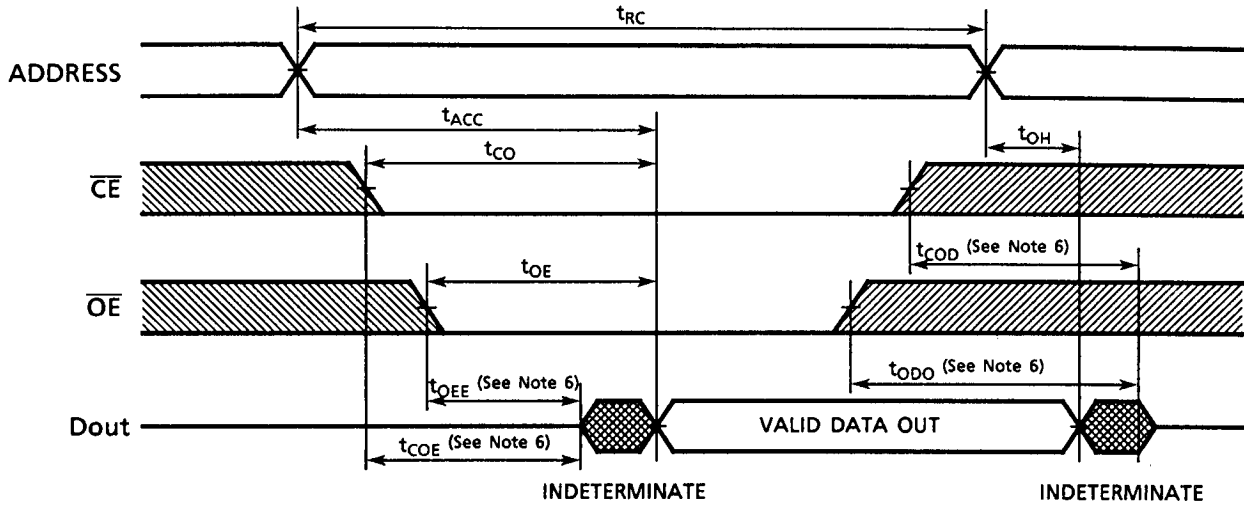
AC TEST CONDITIONS

Input Pulse Level	3.0V/0.0V
Input Pulse Rise and Fall Time	2ns
Input Timing Measurement Reference Level	1.5V
Output Timing Measurement Reference Level	1.5V
Output Load	Fig. 1

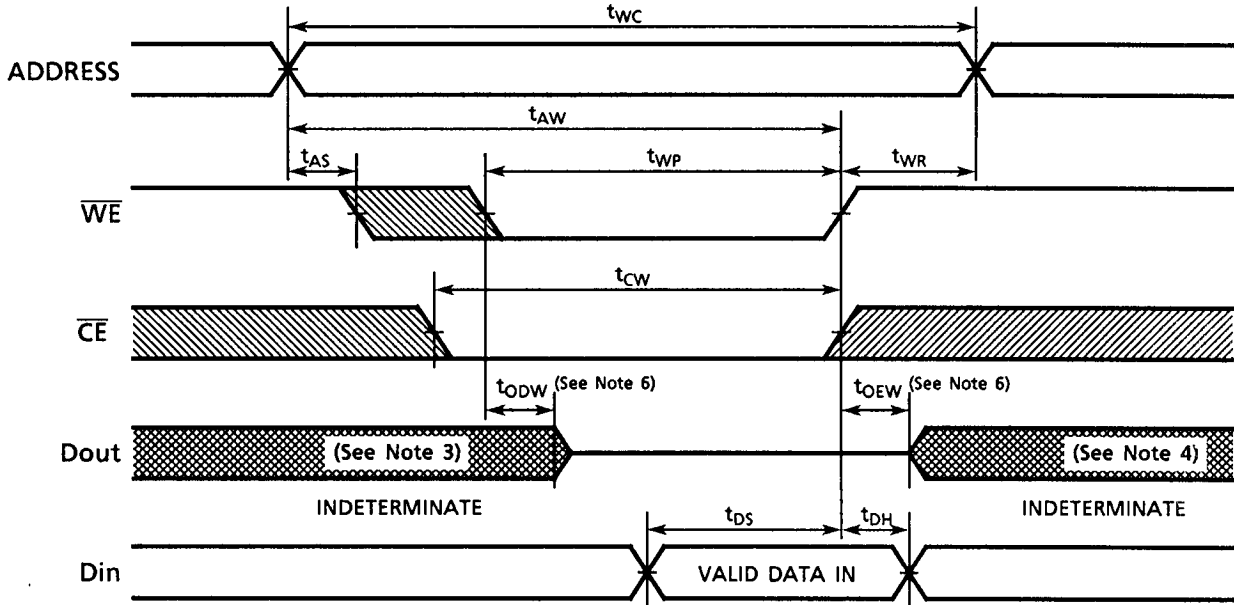
Fig. 1



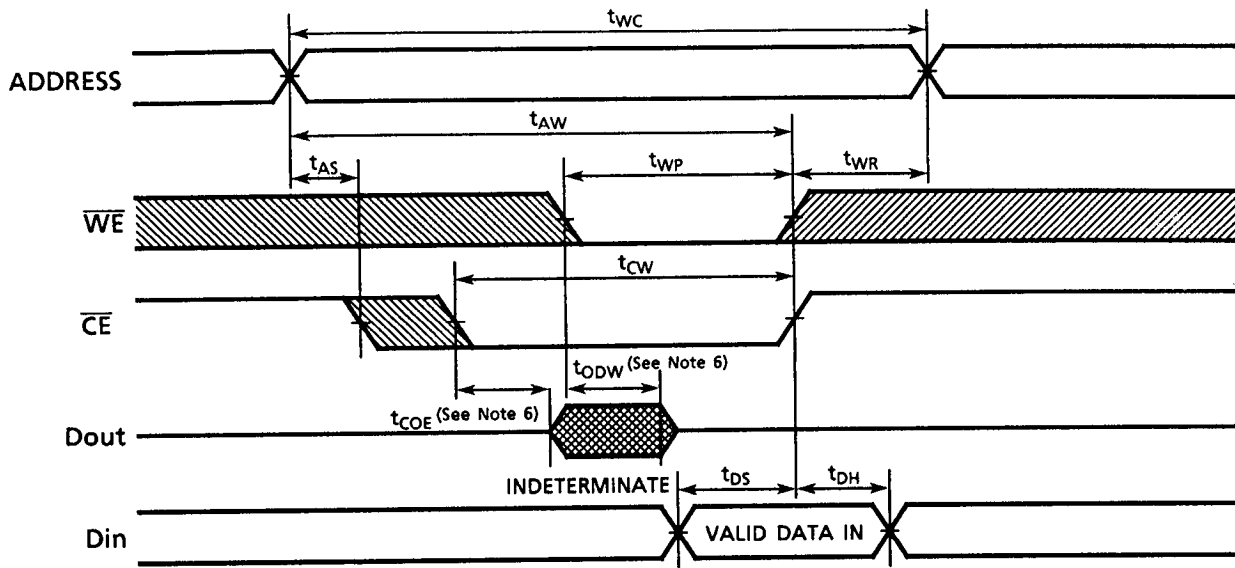
TIMING DIAGRAMS
READ CYCLE (See Note 2)



WRITE CYCLE 1 (\overline{WE} CONTROLLED) (See Note 5)



WRITE CYCLE 2 (\overline{CE} CONTROLLED) (See Note 5)



Note: (1) Operating temperature (T_a) is guaranteed for transverse air flow exceeding 400 linear feet per minute.

(2) \overline{WE} remains HIGH for the Read Cycle.

(3) If \overline{CE} goes LOW coincident with or after \overline{WE} goes LOW, the outputs will remain at high impedance.

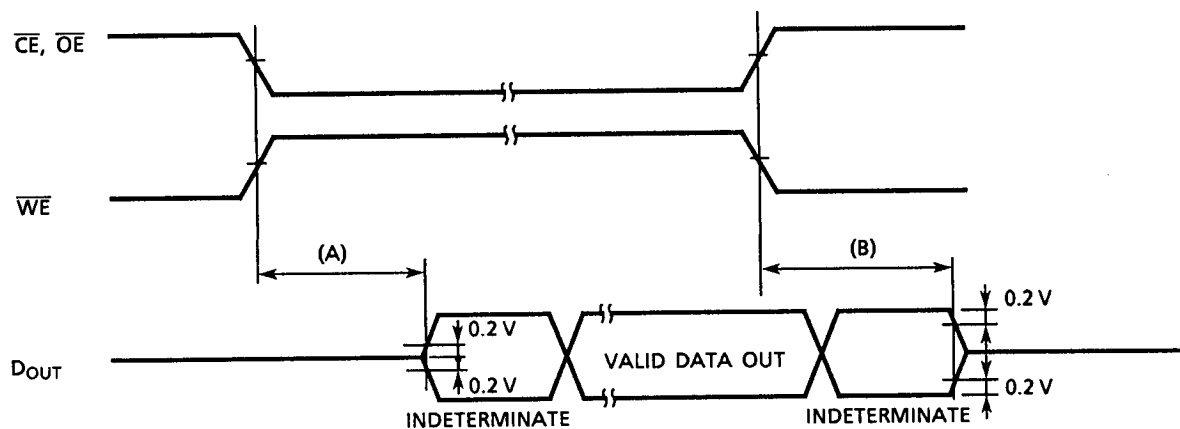
(4) If \overline{CE} goes HIGH coincident with or before \overline{WE} goes HIGH, the outputs will remain at high impedance.

(5) If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.

(6) The parameters specified below are measured using the load shown in Fig. 1.

(A) $t_{COE}, t_{OEE}, t_{OEW}$ Output Enable Time

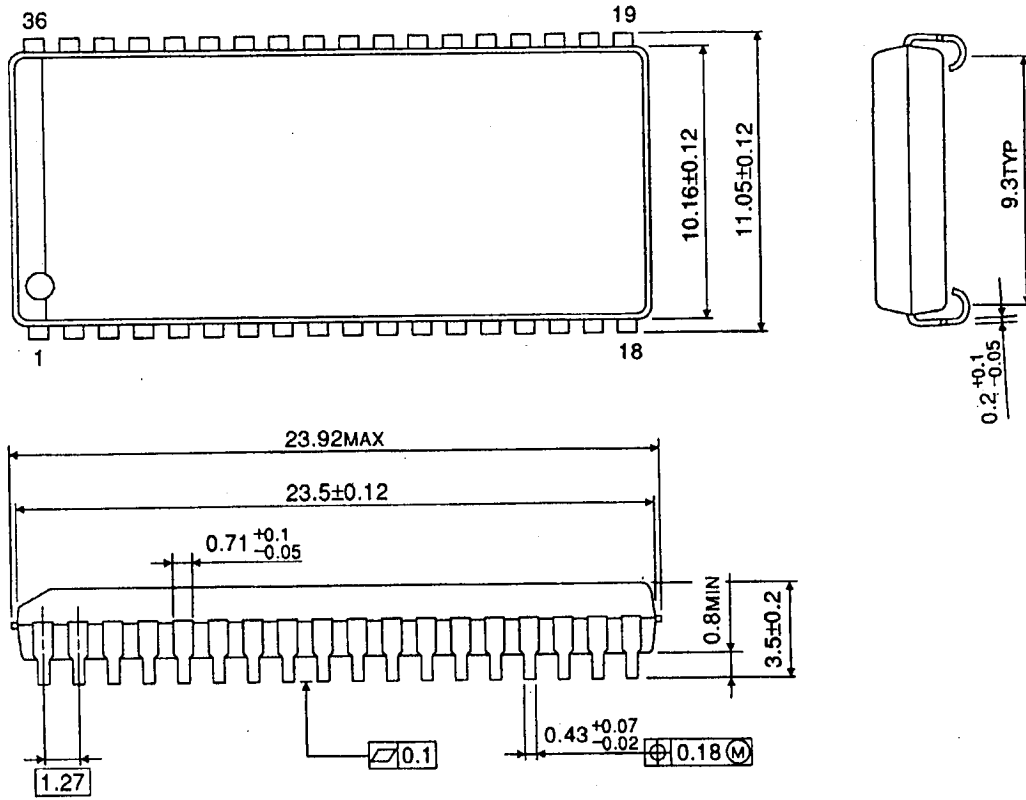
(B) $t_{COD}, t_{ODO}, t_{ODW}$ Output Disable Time



PACKAGE DIMENSIONS

Plastic SOJ (SOJ36-P-400-1.27)

Unit in mm

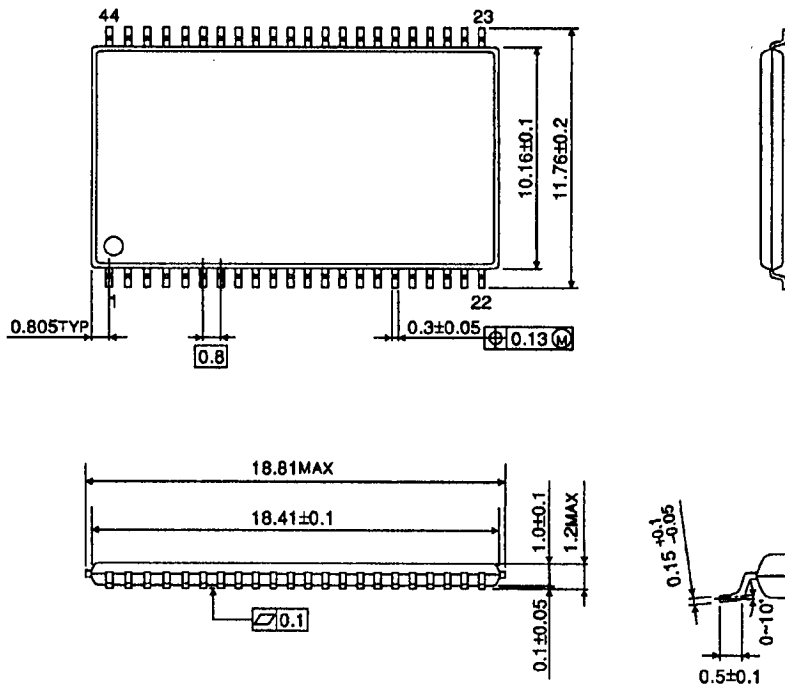


Weight : 1.35g (Typ)

PACKAGE DIMENSIONS

Plastic TSOP (TSOPII 44-P-400-0.80)

Unit in mm



Weight : 0.45g (Typ)